



STP45NF06L STB45NF06L

N-CHANNEL 60V - 0.022Ω - 38A TO-220 / D²PAK
STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP45NF06L	60 V	< 0.028Ω	38 A
STB45NF06L	60 V	< 0.028Ω	38 A

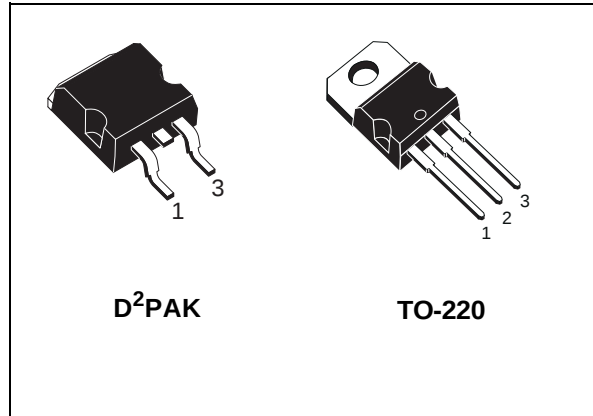
- TYPICAL R_{DS(on)} = 0.022Ω
- EXCEPTIONAL dv/dt CAPABILITY
- LOGIC LEVEL GATE DRIVE

DESCRIPTION

This Power Mosfet is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

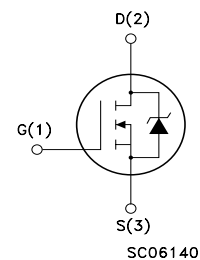
- HIGH-EFFICIENCY DC-DC CONVERTERS
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS



D²PAK

TO-220

INTERNAL SCHEMATIC DIAGRAM



SC06140

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate- source Voltage	±16	V
I _D	Drain Current (continuous) at T _C = 25°C	38	A
I _D	Drain Current (continuous) at T _C = 100°C	26	A
I _{DM} (●)	Drain Current (pulsed)	152	A
P _{TOT}	Total Dissipation at T _C = 25°C	80	W
	Derating Factor	0.53	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	7	V/ns
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Max. Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 38A, di/dt ≤ 300A/μs, V_{DD} ≤ V(BR)DSS, T_j ≤ T_{JMAX}.

STP45NF06L - STB45NF06L

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	1.87	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _I	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	38	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	135	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED) OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±16V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	1	1.7	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 5 V, I _D = 19 A V _{GS} = 10V, I _D = 19 A		0.024 0.022	0.03 0.028	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} = 15V, I _D = 19 A		24		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1600		pF
C _{oss}	Output Capacitance			217		pF
C _{rss}	Reverse Transfer Capacitance			62		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30V, I_D = 19A$		30		ns
t_r	Rise Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		105		ns
Q_g	Total Gate Charge	$V_{DD} = 48V, I_D = 38A,$		23	31	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 5V$		7		nC
Q_{gd}	Gate-Drain Charge			10		nC

SWITCHING OFF

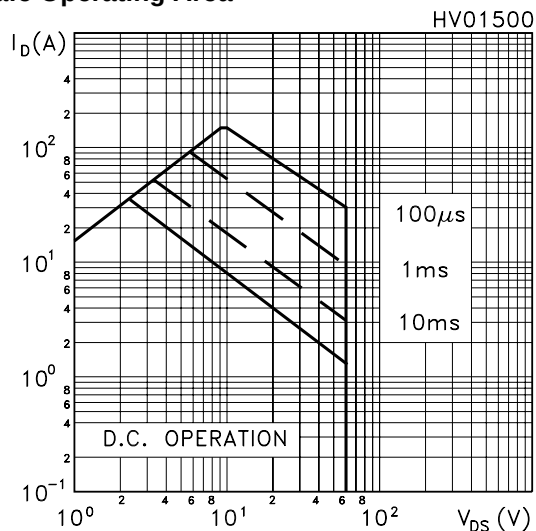
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off-Delay Time	$V_{DD} = 30V, I_D = 19A,$		65		ns
t_f	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3)		25		ns
$t_{d(off)}$	Off-voltage Rise Time	$V_{clamp} = 48V, I_D = 38A$		50		ns
t_f	Fall Time	$R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5)		55		ns
t_c	Cross-over Time			85		ns

SOURCE DRAIN DIODE

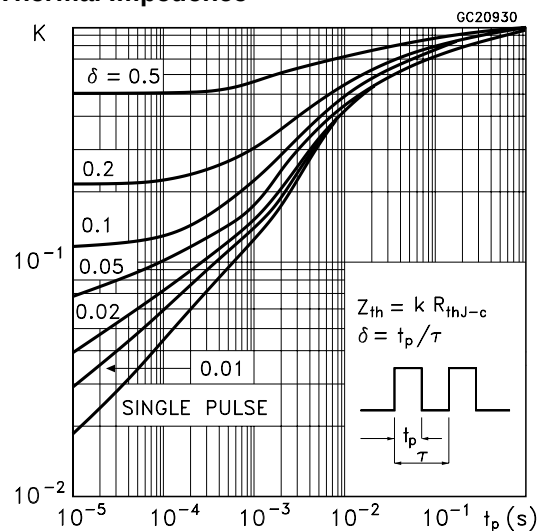
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				38	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				152	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 38A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 38A, di/dt = 100A/\mu s,$		70		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 100V, T_J = 150^\circ C$		110		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		4		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

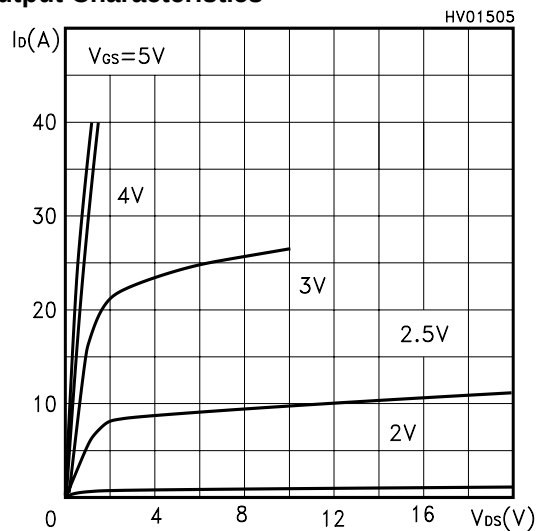
Safe Operating Area



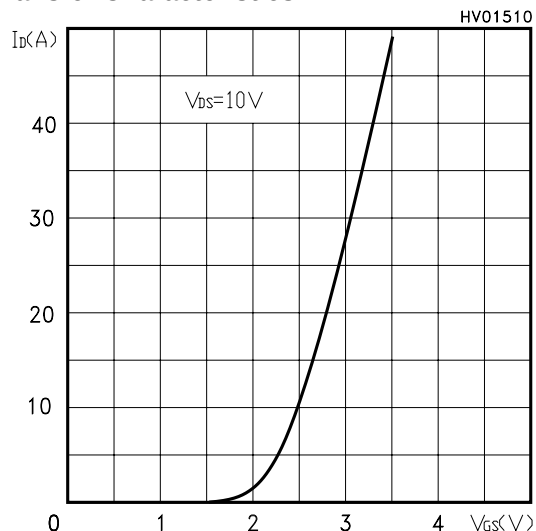
Thermal Impedance



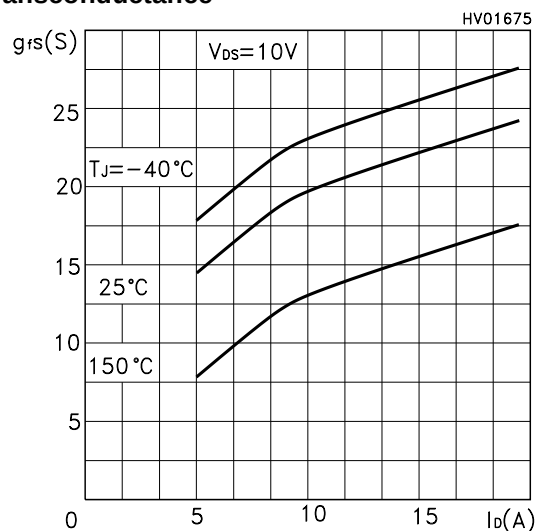
Output Characteristics



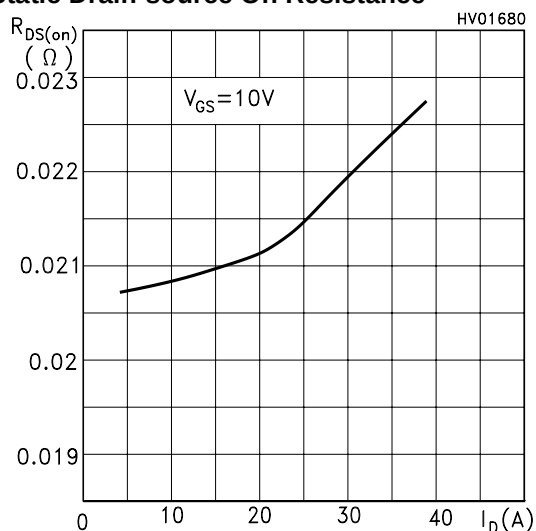
Transfer Characteristics



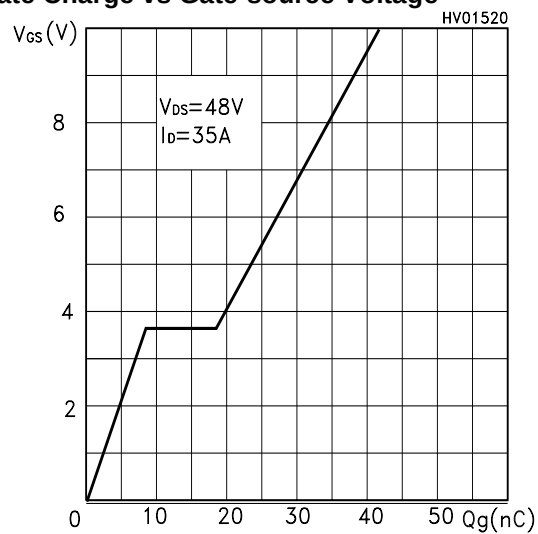
Transconductance



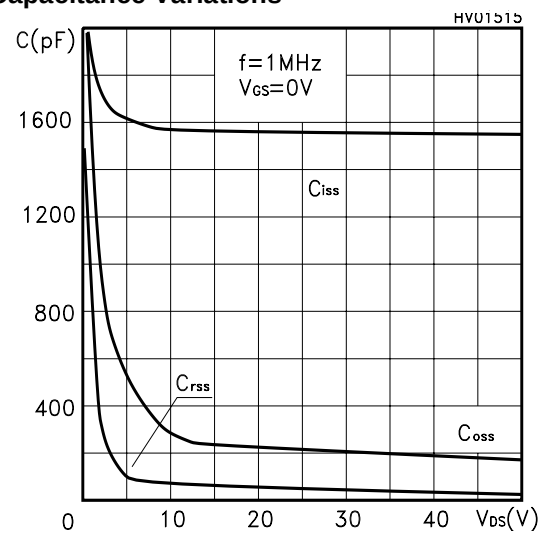
Static Drain-source On Resistance



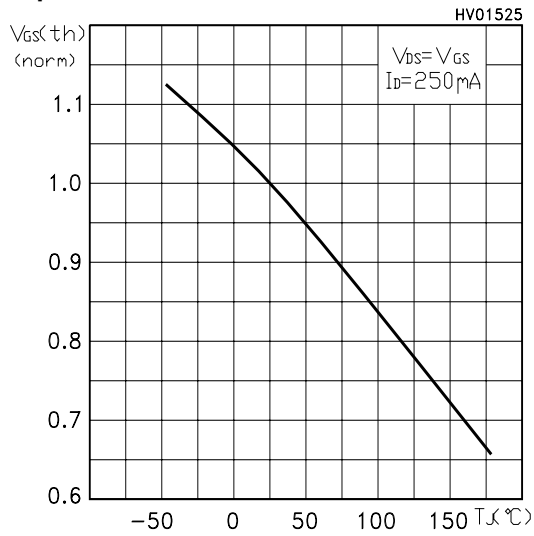
Gate Charge vs Gate-source Voltage



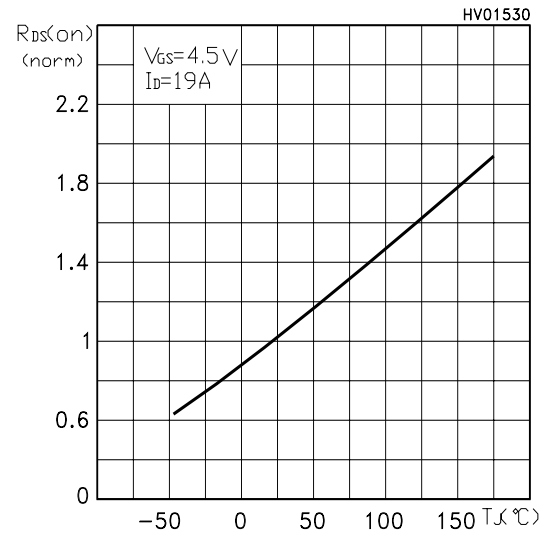
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

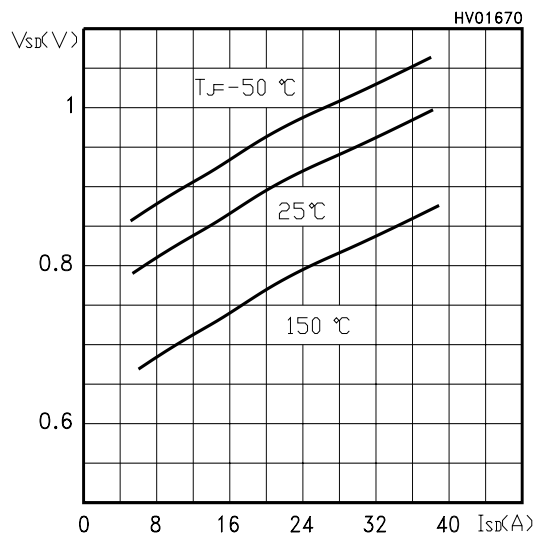


Fig. 1: Unclamped Inductive Load Test Circuit

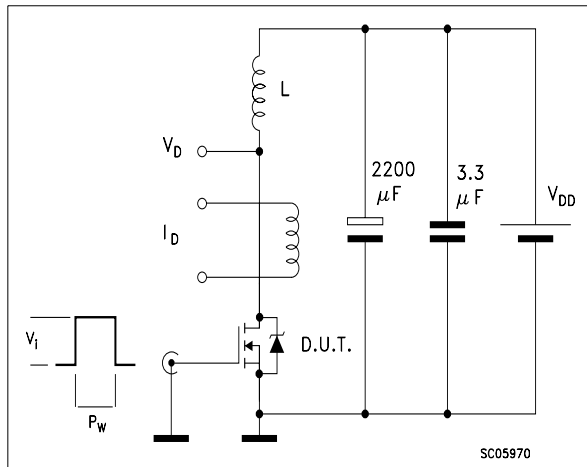


Fig. 2: Unclamped Inductive Waveform

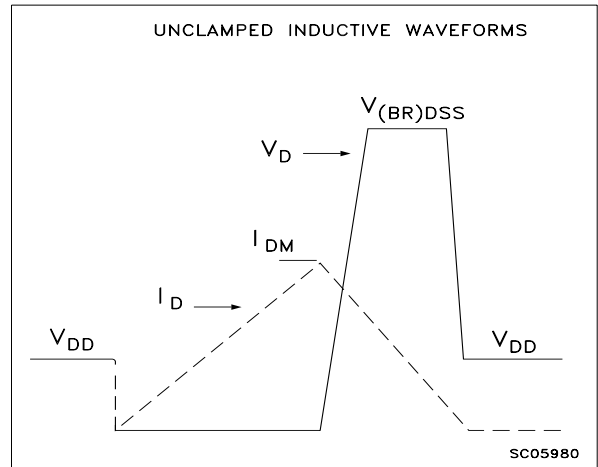


Fig. 3: Switching Times Test Circuit For Resistive Load

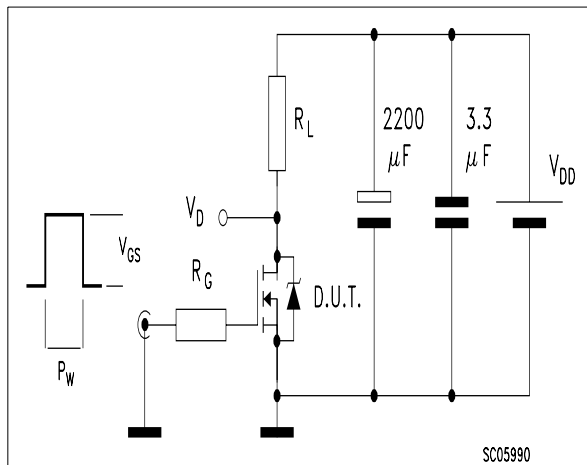


Fig. 4: Gate Charge test Circuit

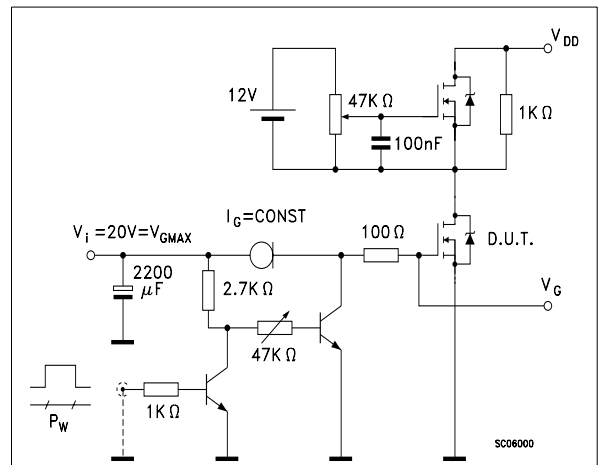
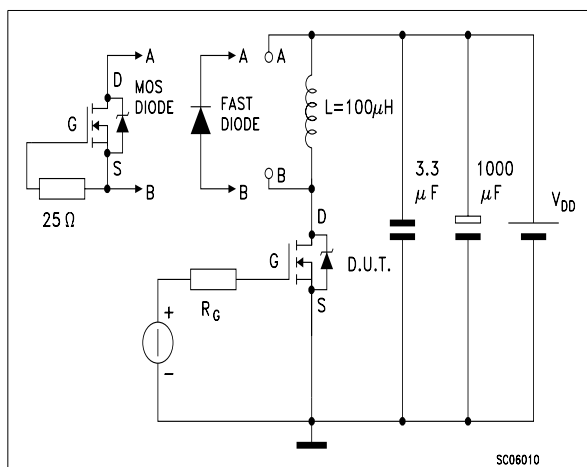
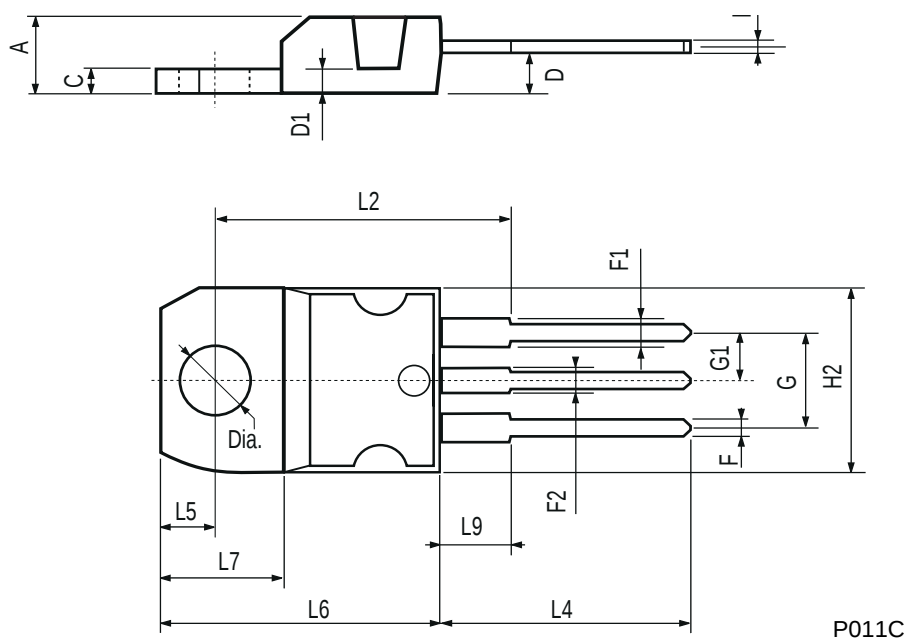


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



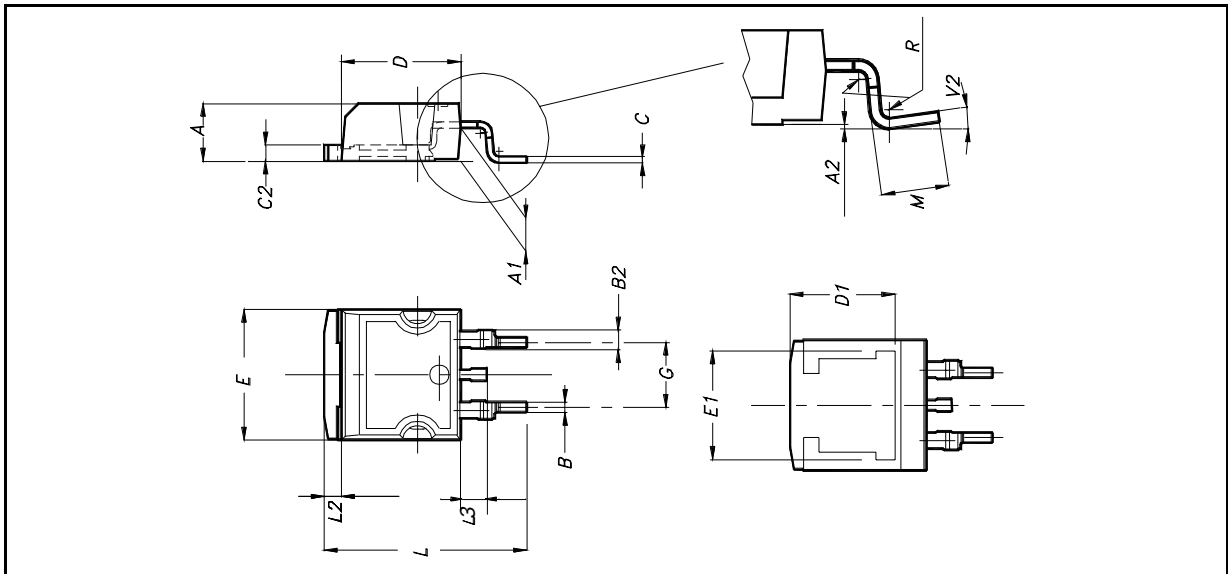
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



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